



### General Description

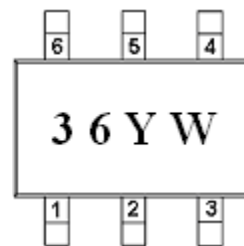
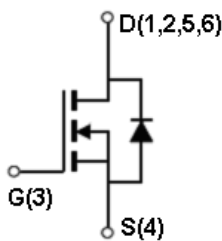
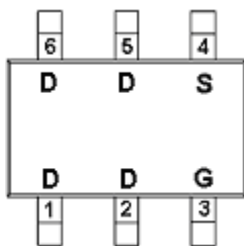
AFN3436, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

### Features

- 30V/3.6A,  $R_{DS(ON)}=72m\Omega@V_{GS}=10V$
- 30V/3.0A,  $R_{DS(ON)}=82m\Omega@V_{GS}=4.5V$
- 30V/2.2A,  $R_{DS(ON)}=160m\Omega@V_{GS}=2.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- TSOP-6 package design

### Pin Description ( TSOP-6 )



### Application

- Portable Equipment
- Battery Powered System
- Net Working System

### Pin Define

Pin	Symbol	Description
1	D	Drain
2	D	Drain
3	G	Gate
4	S	Source
5	D	Drain
6	D	Drain

### Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN3436TS6RG	36YW	TSOP-6	Tape & Reel	3000 EA

- ※ 36 parts code
- ※ Y year code ( 0 ~ 9 )
- ※ W week code ( A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52 )
- ※ AFN3436TS6RG : 7" Tape & Reel ; Pb- Free ; Halogen- Free



### Absolute Maximum Ratings

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V <sub>DSS</sub>	30	V
Gate –Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	3.6
		T <sub>A</sub> =70°C	3.0
Pulsed Drain Current	I <sub>DM</sub>	20	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	1.6	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	2.0
		T <sub>A</sub> =70°C	1.3
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	120	°C/W

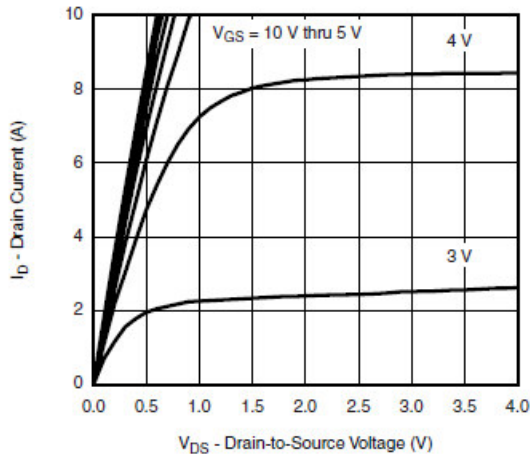
### Electrical Characteristics

(T<sub>A</sub>=25°C Unless otherwise noted)

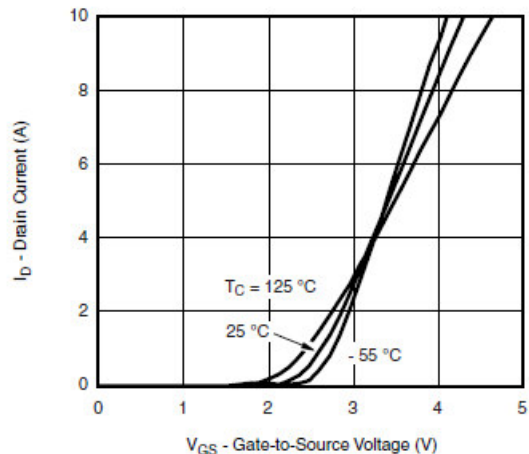
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30			V
Gate Threshold Voltage	V <sub>G(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.5		1.5	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±16V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V			1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			30	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5V, V <sub>GS</sub> =4.5V	30			A
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3.6A		60	72	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.0A		70	82	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.2A		140	160	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =6.1A		20		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.7A, V <sub>GS</sub> =0V		0.8	1.2	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V I <sub>D</sub> ≧3.6A		2.3	3	nC
Gate-Source Charge	Q <sub>gs</sub>			1.0		
Gate-Drain Charge	Q <sub>gd</sub>			0.6		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V f=1MHz		280		pF
Output Capacitance	C <sub>oss</sub>			40		
Reverse Transfer Capacitance	C <sub>rss</sub>			20		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, R <sub>L</sub> =15Ω I <sub>D</sub> ≧1.0A, V <sub>GEN</sub> =10V R <sub>G</sub> =6Ω		10	15	ns
	t <sub>r</sub>			12	20	
Turn-Off Time	t <sub>d(off)</sub>			15	25	
	t <sub>f</sub>			10	15	



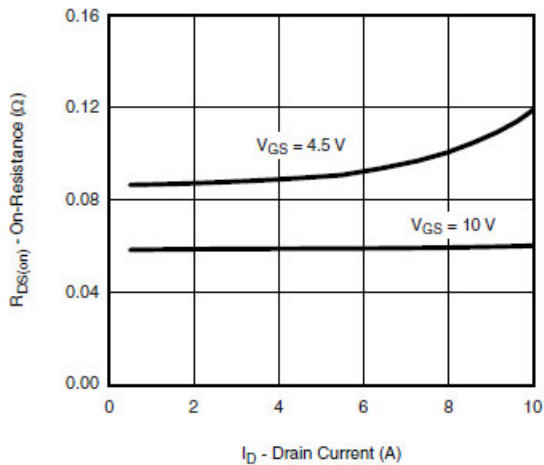
## Typical Characteristics



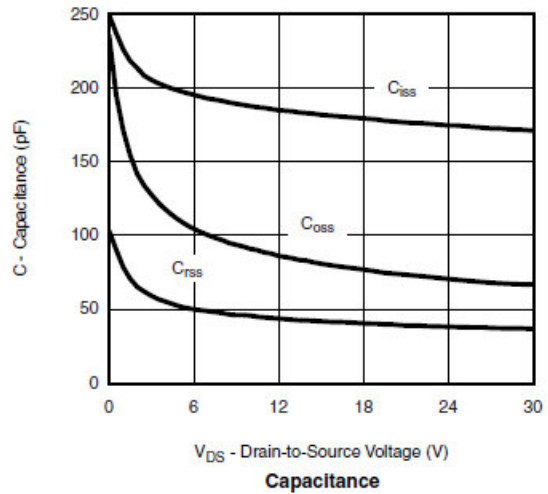
Output Characteristics



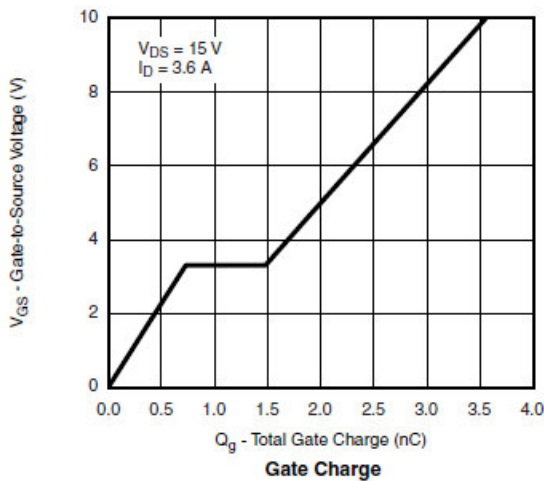
Transfer Characteristics



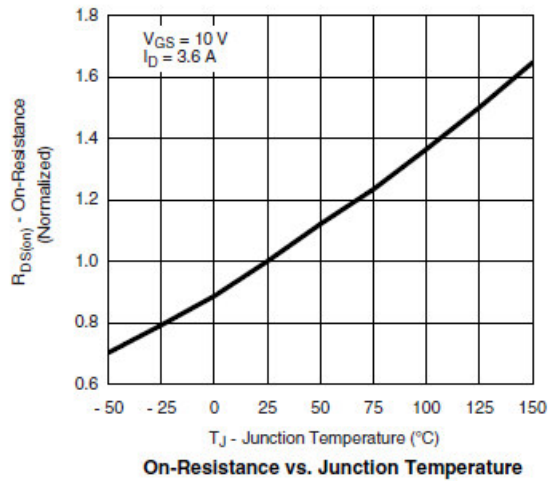
On-Resistance vs. Drain Current



Capacitance



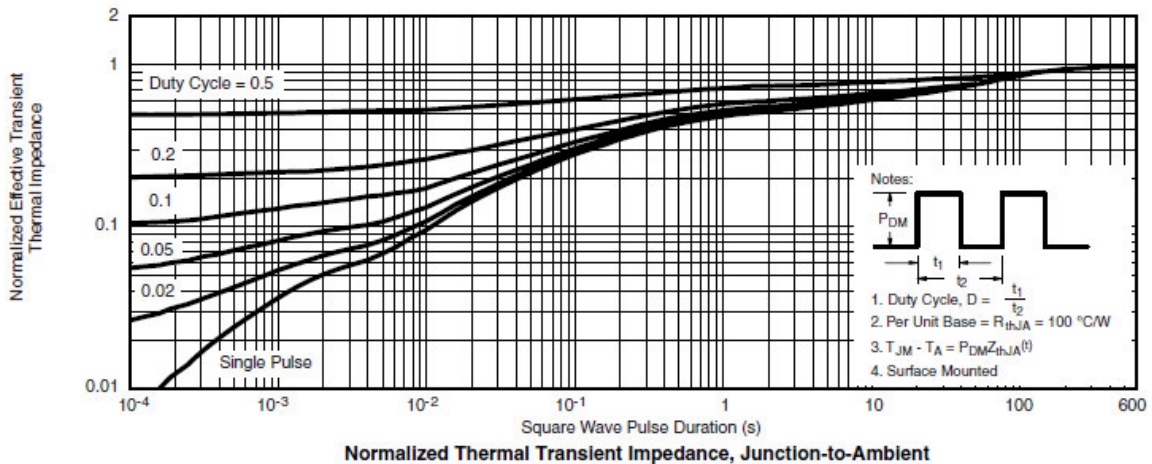
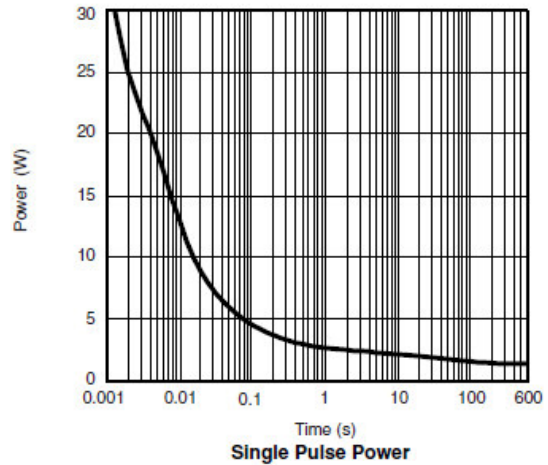
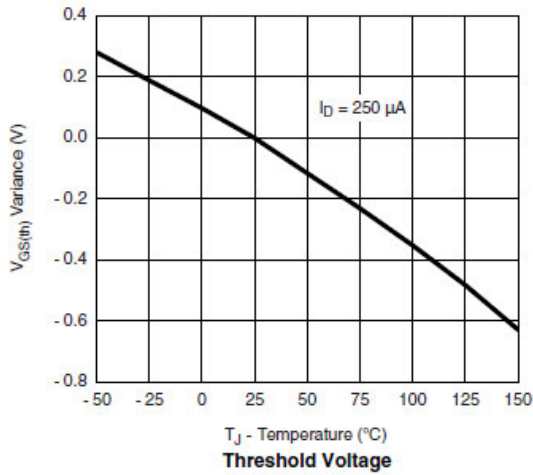
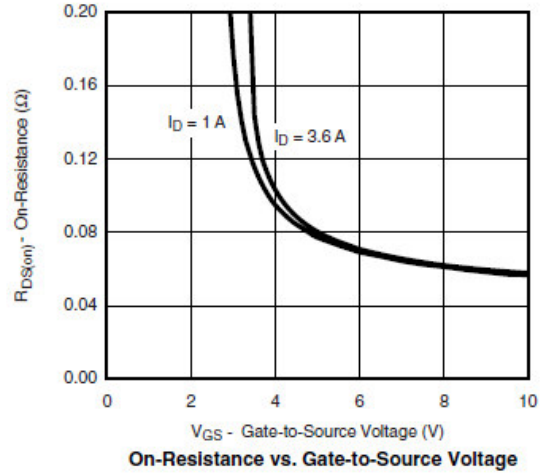
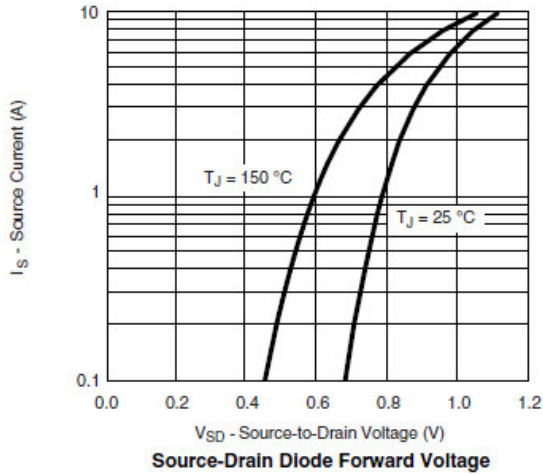
Gate Charge



On-Resistance vs. Junction Temperature



**Typical Characteristics**





**Typical Characteristics**

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

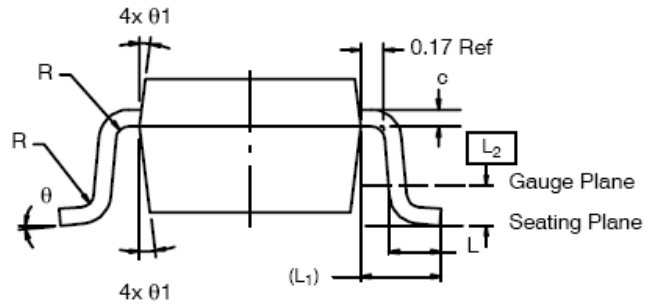
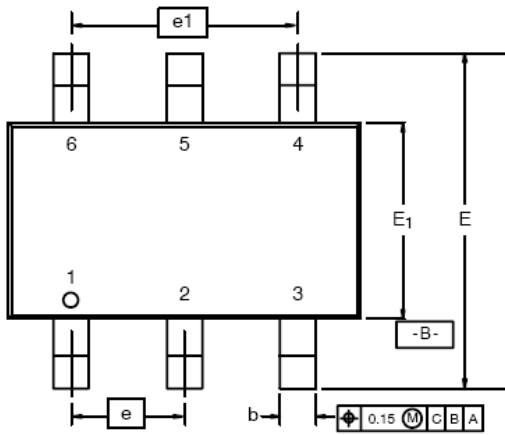


Unclamped Inductive Switching Test Circuit & Waveforms





**Package Information ( TSOP-6 )**



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.96	0.106	0.112	0.117
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067
e	1.00 BSC			0.0394 BSC		
e <sub>1</sub>	1.90	2.00	2.10	0.075	0.080	0.085
L	0.35	-	0.50	0.014	-	0.020
L <sub>1</sub>	0.60 Ref			0.024 Ref		
L <sub>2</sub>	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ <sub>1</sub>	7° Nom			7° Nom		

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